

**REMARKS**

Applicants thank the Examiner for the thorough consideration given the present application.

Claims 1-9 are pending. Claims 1 and 5 are independent. Claim 5 is amended. Reconsideration of this application is respectfully requested.

Drawings

The proposed drawing change is approved. Included with the accompanying Letter to the Official Draftsperson is a revised formal drawing for FIG. 1c which incorporates the approved proposed changes. It is respectfully submitted that the drawings comply with USPTO requirements, and the Examiner is requested to provide a Notice of Draftsperson's Patent Drawing Review, Form PTO-948, confirming approval of the formal drawings by the Official Draftsperson, with the next official communication.

Rejection under 35 U.S.C. §112, second paragraph

Claims 5-9 are rejected under 35 U.S.C. §112, second paragraph, as being indefinite. It is respectfully submitted that amended claim 5 is clear, definite, and provides full support for the elements recited therein. Withdrawal of the

rejection under 35 U.S.C. §112, second paragraph, is, therefore, respectfully requested.

Rejections under 35 U.S.C. §102(e)/§103(a)

Claims 1, 2, and 4 rejected under 35 U.S.C. §102(e) as being anticipated by U.S. Patent No. 6,479,853 to Chisiki. Claim 3 is rejected under 35 U.S.C. §103(a) as being unpatentable over Chishiki in view of U.S. Patent No. 5,705,838 to Jost et al. Claims 5-9 are rejected under 35 U.S.C. §103(a) as being unpatentable over U.S. Patent No. 6,483,138 to Habu et al. in view of U.S. Patent No. 5,790,452 to Lien. These rejections are respectfully traversed.

The primary references of Chishiki and Habu et al. have effective filing dates of September 21, 1998, and June 18, 1997, respectively. However, the priority document for the present application, KR 73475/1996, was filed December 17, 1996. Attached is a verified English language translation of Applicants' priority document, thereby eliminating Chishiki and Habu et al. as references against the present application.

In view of the foregoing, it is respectfully submitted that independent claims 1 and 5 are in condition for allowance and that the dependent claims, which depend directly or indirectly from independent claims 1 and 5, are also allowable for at least

the same reasons, as well as for the additional limitations provided by these claims. Accordingly, all claims are in condition for allowance, and withdrawal is requested of the rejections under 35 U.S.C. §102(e) and §103(a),

Conclusion

All of the stated grounds of rejection have been properly traversed, accommodated, or rendered moot. It is believed that a full and complete response has been made to the outstanding Office Action, and that the present application is in condition for allowance.

However, if there are any outstanding issues, the Examiner is invited to telephone Sam Bhattacharya (Reg. No. 48,107) at 703-205-8000 in an effort to expedite prosecution.

Pursuant to the provisions of 37 CFR 1.17 and 1.136(a), Applicants respectfully petition for a one (1) month extension of time for filing a response in connection with the present application. The required fee of \$110.00 is attached hereto.

Attached hereto is a marked-up version of the changes made to the claim by this Amendment.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17, particularly extension of time fees.

Respectfully submitted,  
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By: 

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**0465-0826P**  
Attachments  
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**MARKED-UP COPY OF AMENDED CLAIM 5**

5. (Amended) An unsymmetrical semiconductor device using a self-aligned contact hole, the device comprising:

a substrate having impurity regions formed therein;

a first conductor structure and a second conductor structure formed on the substrate [except over the substrate in a region between the first and second conductor structures] ;

first sidewall spacers, each first sidewall spacer being formed to abut against both a side of the first or second conductor structures and a side of an insulator structure, the first sidewall spacers manifesting the self-aligned contact hole in the region between the first and second conductor structures; and

second sidewall spacers formed on sides of the first and second conductor structures opposite of the self-aligned contact hole.